

N-Channel Enhancement Mode Power MOSFET

Features

- Excellent package for good heat dissipation
- High density cell design for ultra low R_{DS(on)}
- V_{DS} = 100V, I_{D} = 10A $R_{DS(on)}$ < 120m Ω @V_{GS}= 10V

1. G Applications

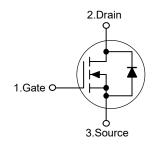
- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



TO-252

1. Gate 2.Drain 3.Sourse

Schematic Diagram



	Marking code											
		10H10: Product code										
		Y: Year code	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
	%\$<%\$ YW		G	н	J	К	А	В	С	D	E	F
	1 **	W: Week code			7~52		53					
		vv. vveek code	C	code		A~Z	-		a~z		z	

Absolute Maximum Ratings

Ratings at 25°C case temperature unless otherwise specified.

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	ID	10	A
Drain Current-Pulsed Note1	I _{DM}	40	А
Single pulse avalanche energy Note2	Eas	4	mJ
Maximum Power Dissipation	P _D	24	W
Junction Temperature	TJ	175	°C
Storage Temperature Range	T _{STG}	-55 to +175	°C

Thermal Characteristics

Thermal Resistance,Junction-to-Case	Rejc	6.3	°C/W
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Electrical Characteristics

(T_J=25°C unless otherwise specified)

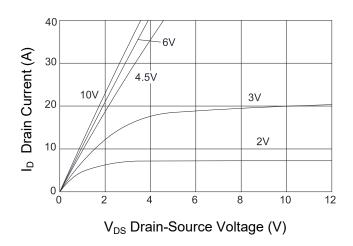
Parameter	Symbol	Test Condition	Min.	Тур.	Max.	Unit	
Static Characteristics			1				
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V,I _D =250µA	100			V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V,V _{GS} =0V			1	μA	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V			±100	nA	
Gate Threshold Voltage Note3	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	1	1.5	2.5	V	
Duain Course On Desigtenes Note3	D	V _{GS} =10V,I _D =8A		98	120	mΩ	
Drain-Source On-Resistance Note3	R _{DS(on)}	V _{GS} =4.5V,I _D =5A		100	140	mΩ	
Forward Transconductance Note3	G FS	V _{DS} =5V,I _D =3A		8		S	
Dynamic Characteristics							
Input Capacitance	Ciss			825		pF	
Output Capacitance	Coss	V _{DS} =30V,V _{GS} =0V,f=1MHz		37.5		pF	
Reverse Transfer Capacitance	C _{rss}			31.5		pF	
Gate Resistance	Rg	V _{DS} =0V,V _{GS} =0V,f=1MHz		1		Ω	
Switching Characteristics							
Turn-on Delay Time	t _{d(on)}			7.5		nS	
Turn-on Rise Time	t _r	V _{DS} =50V, I _D =3A		6		nS	
Turn-off Delay Time	t _{d(off)}	V_{GS} =10V, R_{G} =1.8 Ω		21		nS	
Turn-off Fall Time	t _f			9		nS	
Total Gate Charge	Qg			18		nC	
Gate-Source Charge	Q _{gs}	V _{DS} =30V,I _D =2A, V _{GS} =10V		2.5		nC	
Gate-Drain Charge	Q _{gd}			4		nC	
Source-Drain Diode Characteristics							
Diode Forward Voltage	V _{SD}	V _{GS} =0V,I _S =10A		0.9	1.2	V	
Diode Forward Current	Is				10	Α	

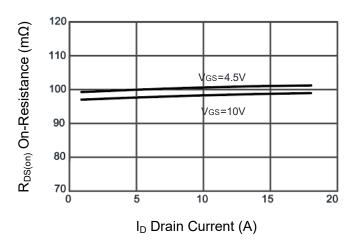
Note: 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

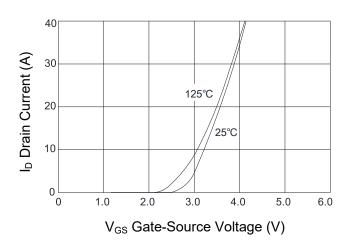
- $2. \ E_{AS} \ condition: T_J = 25^{\circ}C, V_{DD} = 50V, V_{GS} = 10V, L = 0.5mH, R_g = 25\Omega, I_{AS} = 4A.$
- 3. Pulse Test: Pulse width≤300µs, duty cycle≤0.5%.

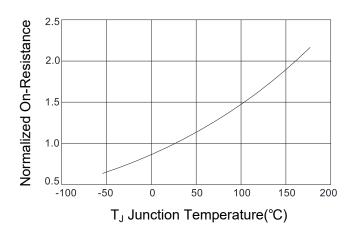


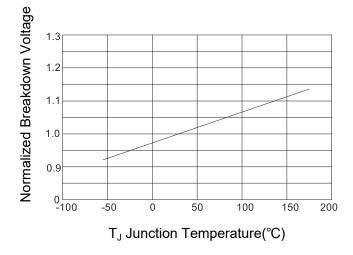
Typical Characteristic Curves

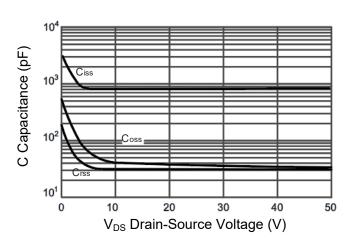




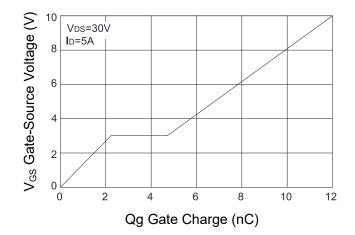


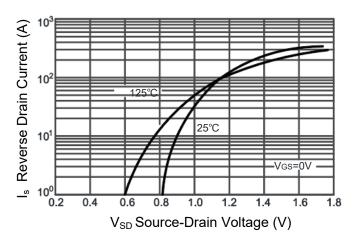


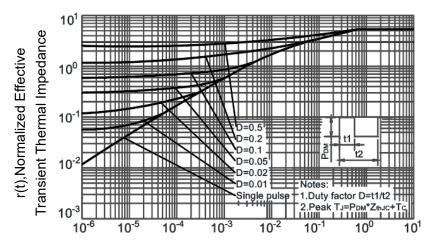




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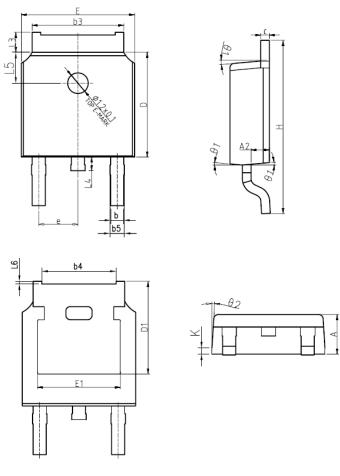


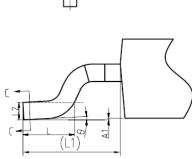
Square Wave Pluse Duration(sec)



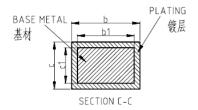
Package Outline

TO-252 Dimensions in mm





Cymphal		mm			
Symbol	Min.	Nom.	Max.		
*A	2.20	2.30	2.38		
*A1	0.00		0.10		
A2	0.97	1.07	1.17		
*b	0.72	0.78	0.85		
b1	0.71	0.76	0.81		
*b3	5.23	5.33	5.46		
b4	4.27	4.32	4.37		
b5	0.72				
*c	0.47	0.53	0.58		
c1	0.46	0.51	0.56		
*D	6.00	6.00 6.10			
D1	5.30REF				
*E	6.50	6.60	6.70		
E1	4.70	4.83	4.92		
*e	2.286BSC				
*H	9.90	10.10	10.30		
L	1.40	1.50	1.70		
L1	2.90REF				
L2		0.51BSC			
*L3	0.90		1.25		
*L4	0.60	0.80	1.00		
L5	1.70	1.80	1.90		
L6	0	0.047	0.123		
θ	0°		8°		
*θ1	5°	7°	9°		
θ2	5°	7°	9°		
K	0.40REF				
带*为检验尺寸					



Ordering Information

Device	Package	Shipping
TN10H10NTE	TO-252	2,500PCS/Reel&13inches



TN10H10NTE

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Contact Information

For additional information, please contact your local Sales Representative.



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Product Specification Statement

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